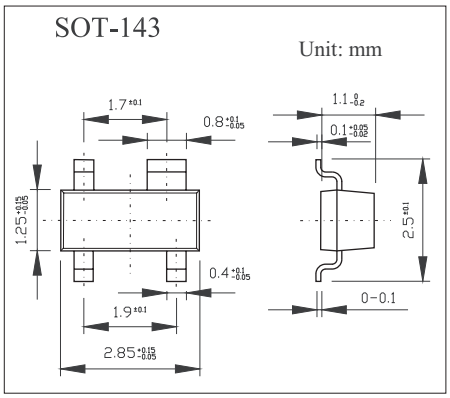
High-Speed Double Diode

BAS28



Features

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage:max. 75 V
- Repetitive peak reverse voltage:max. 85 V
- Repetitive peak forward current:max. 500 mA .

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Test Condition	MIN	MAX	Unit
repetitive peak reverse voltage	V_{RMM}	200		85	V
continuous reverse voltage	V_R	100		75	V
continuous forward current	I_F	250		210	mA
repetitive peak forward current	I_{FRM}	150		500	mA
non-repetitive peak forward current	I_{FSM}	square wave; T_j = 25 ℃ prior to surge			A
		t = 1 μs		4	
		t = 1 ms		1	
		t = 1 s		0.5	
total power dissipation	P_{tot}	T_{amb} = 25℃	-65	250	mW
storage temperature	T_{stg}			+150	℃
junction temperature	T_j			150	℃

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Max	Unit
forward voltage	V_F	I_F = 1 mA		715	mV
		I_F = 10 mA		855	mV
		I_F = 50 mA		1	V
		I_F =150 mA		1.25	V
reverse current	I_R	V_R = 25 V		30	nA
		V_R = 75 V		1	μA
		V_R = 25 V; T_j = 150℃		30	μA
		V_R = 75 V; T_j = 150℃		50	μA
diode capacitance	C_d	f = 1 MHz; V_R = 0		1.5	pF
reverse recovery time	t_{rr}	when switched from I_F = 10 mA to I_R = 10 mA;		4	ns
		R_L = 100Ω measured at I_R = 1 mA;			
forward recovery voltage	V_{fr}	when switched from IF = 10 mA;t_r = 20 ns;		1.75	V

■ Marking

Marking	JT